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N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = 25°C
60V	$7.5\Omega @ V_{GS} = 5V$	115mA

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc



SOT523

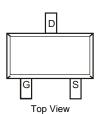
Top View

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead Free, Full RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Notes 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approximate)



Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
2N7002T-7-F	Commercial	SOT523	3,000/Tape & Reel
2N7002T-13-F	Commercial	SOT523	10,000/Tape & Reel
2N7002TQ-7-F	Automotive	SOT523	3,000/Tape & Reel
2N7002TQ-13-F	Automotive	SOT523	10,000/Tape & Reel

Equivalent Circuit

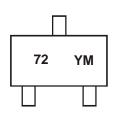
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free

2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

3. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants

4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



72 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006)

M = Month (ex: 9 = September)

Date Code Key

2410 0040 110)												
Year	2005		2006	2007		2008	2009		2010	2011		2012
Code	S		Т	U		V	W		Х	Y		Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	60	V	
Drain-Gate Voltage R _{GS} ≤ 1.0M	Ω	V _{DGR}	60	V	
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V	
Drain Current (Note 5)	Continuous Continuous @ 100°C Pulsed	I _D	115 73 800	mA	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	Pd	150	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	833	°C/W
Operating and Storage Temperature Range	T _{j,} T _{STG}	-55 to +150	°C

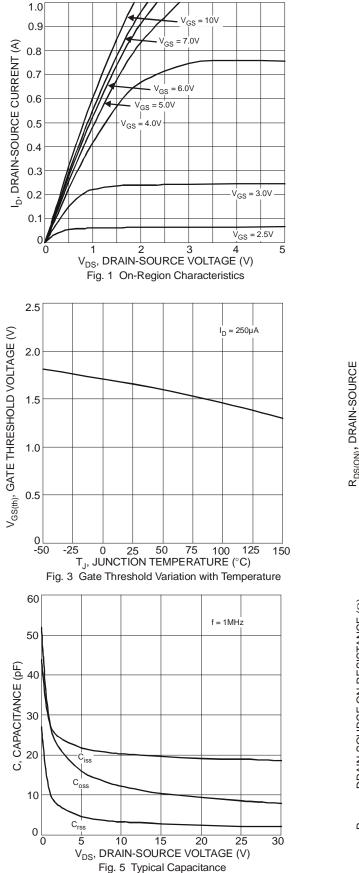
Electrical Characteristics @T_A = 25°C unless otherwise specified

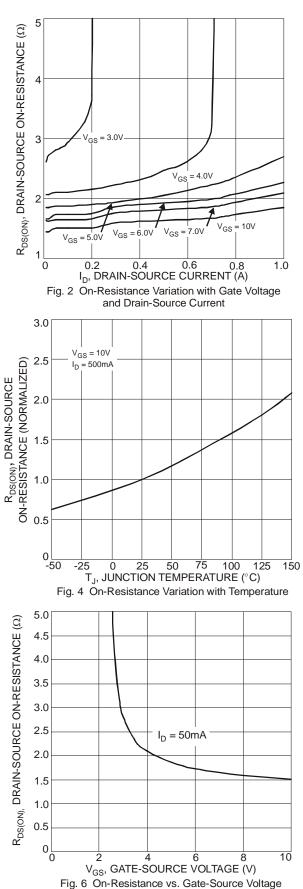
Characteristi	c	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)							•
Drain-Source Breakdown Voltage		BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = 25^{\circ}C$ @ $T_C = 125^{\circ}C$		I _{DSS}	_	_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _i = 25°C @ T _i = 125°C	R _{DS (ON)}	_	2.0 4.4	7.5 13.5	Ω	$V_{GS} = 5.0$ V, $I_D = 0.05$ A $V_{GS} = 10$ V, $I_D = 0.5$ A
On-State Drain Current		I _{D(ON)}	0.5	1.0			$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g _{FS}	80	_	—	mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS (Note	7)						·
Input Capacitance		Ciss	_	22	50	pF	
Output Capacitance Reverse Transfer Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
		C _{rss}	_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS (Not	te 7)						·
Turn-On Delay Time		t _{D(ON)}		7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}	_	11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. 6 .Short duration pulse test used to minimize self-heating effect. Notes:

7. Guaranteed by design. Not subject to production testing.

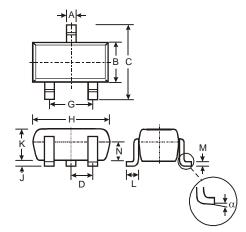






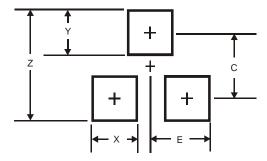


Package Outline Dimensions



	SOT523							
Dim	Min	Max	Тур					
Α	0.15	0.30	0.22					
В	0.75	0.85	0.80					
С	1.45	1.75	1.60					
D	_	_	0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
J	0.00	0.10	0.05					
K	0.60	0.80	0.75					
L	0.10	0.30	0.22					
М	0.10	0.20	0.12					
Ν	0.45	0.65	0.50					
α	0°	8°	_					
All	All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)				
Z	1.8				
Х	0.4				
Y	0.51				
С	1.3				
E	0.7				



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